

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-6.0	V
Collector Current	I _C	-600	mA
Peak Collector Current	I _{CM}	-800	mA
Peak Base Current	I _{BM}	-200	mA

Thermal Characteristics

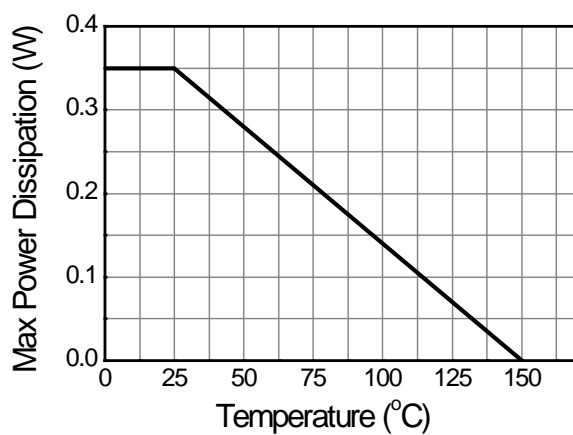
Characteristic	Symbol	Value	Unit
Collector Power Dissipation	P _D	310	mW
		350	
Thermal Resistance, Junction to Ambient	R _{θJA}	403	°C/W
		357	
Thermal Resistance, Junction to Leads	R _{θJL}	350	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

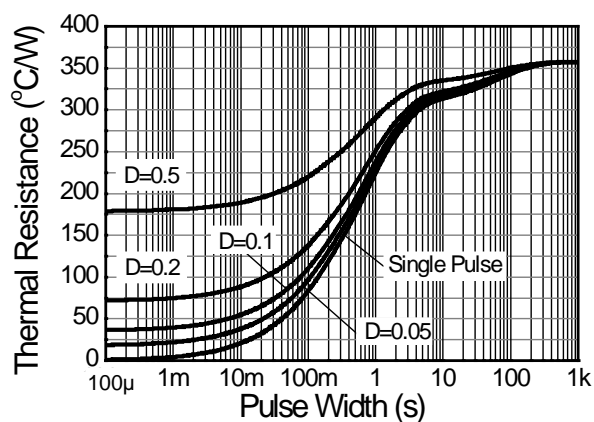
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as Note 6, except the device is mounted on 15 mm x 15mm 1oz copper.
 8. Thermal resistance from junction to solder-point (at the end of the leads).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

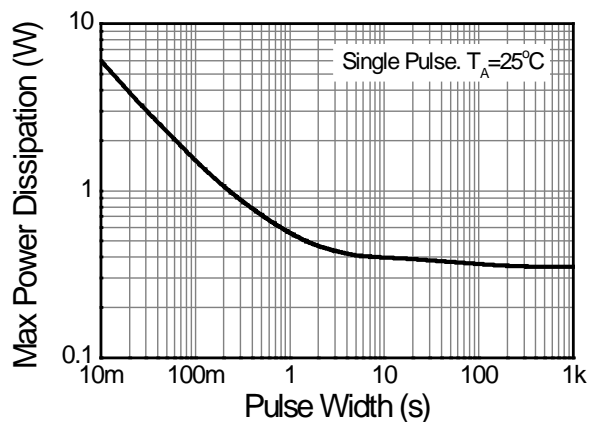
Thermal Characteristics and Derating Information



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	-60	—	V	I _C = -100μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-60	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-6.0	—	V	I _E = -100μA, I _C = 0
Collector Cut-Off Current	I _{CBO}	—	-10	nA μA	V _{CB} = -50V, I _E = 0 V _{CB} = -50V, I _E = 0, T _A = +125°C
Collector Cut-Off Current	I _{CEX}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -0.5V
Base Cut-Off Current	I _{BL}	—	-50	nA	V _{CE} = -30V, V _{EB(OFF)} = -0.5V
Emitter Cut-Off Current	I _{EBO}	—	-50	nA	V _{EB} = -6.0V
ON CHARACTERISTICS (Note 10)					
DC Current Gain	h _{FE}	75 100 100 100 50	— — — 300 —	—	I _C = -100μA, V _{CE} = -10V I _C = -1.0mA, V _{CE} = -10V I _C = -10mA, V _{CE} = -10V I _C = -150mA, V _{CE} = -10V I _C = -500mA, V _{CE} = -10V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.4 -1.6	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-1.3 -2.6	V	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	8.0	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	30	pF	V _{EB} = -2.0V, f = 1.0MHz, I _C = 0
Current Gain-Bandwidth Product	f _T	200	—	MHz	V _{CE} = -20V, I _C = -50mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t _{ON}	—	45	ns	V _{CC} = -30V, I _C = -150mA, I _{B1} = -15mA
Delay Time	t _D	—	10	ns	
Rise Time	t _R	—	40	ns	
Turn-Off Time	t _{OFF}	—	100	ns	V _{CC} = -6.0V, I _C = -150mA, I _{B1} = I _{B2} = -15mA
Storage Time	t _S	—	80	ns	
Fall Time	t _F	—	30	ns	

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

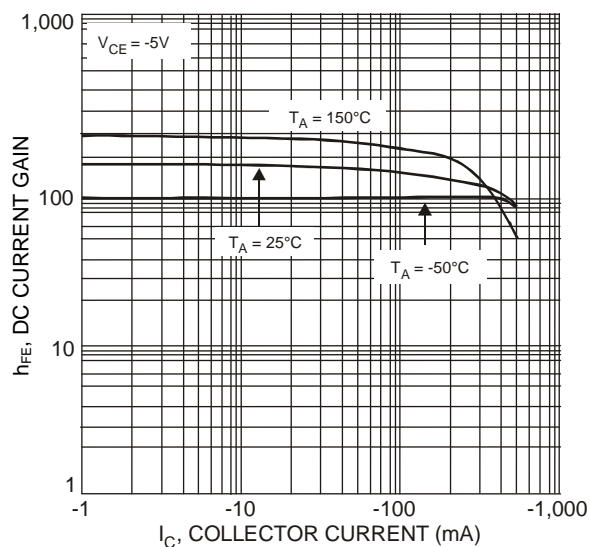


Fig. 1 Typical DC Current Gain vs. Collector Current

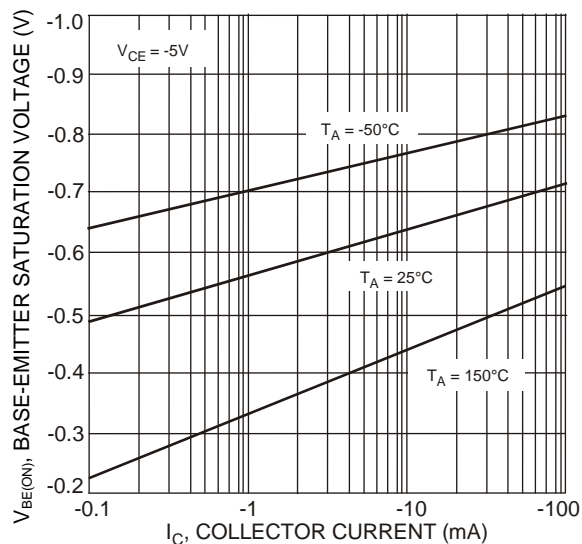


Fig. 2 Typical Base-Emitter Saturation Voltage vs. Collector Current

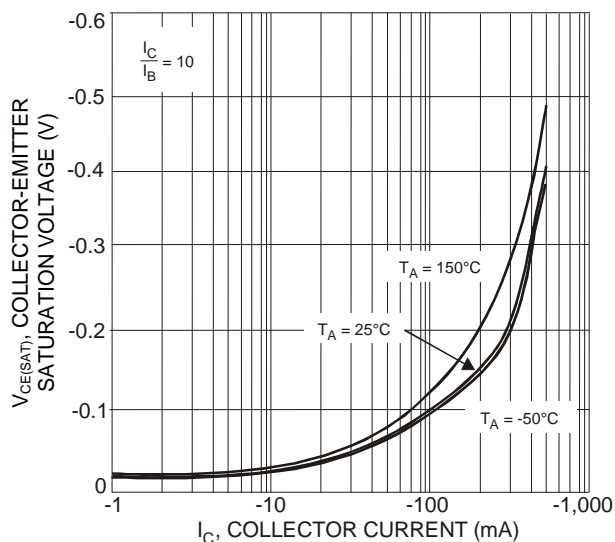


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

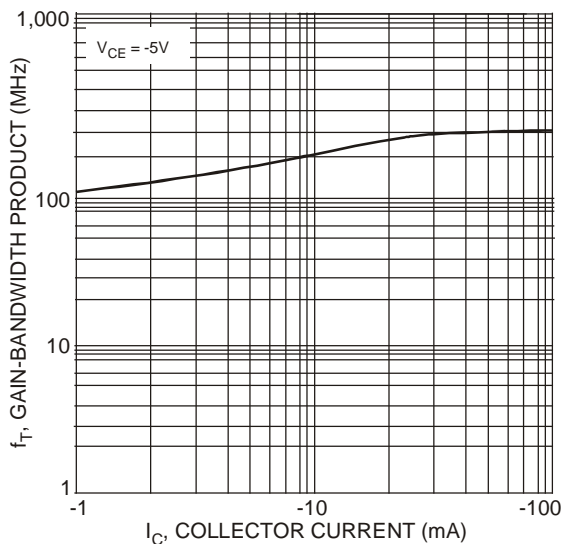


Fig. 4 Typical Gain-Bandwidth Product vs. Collector Current

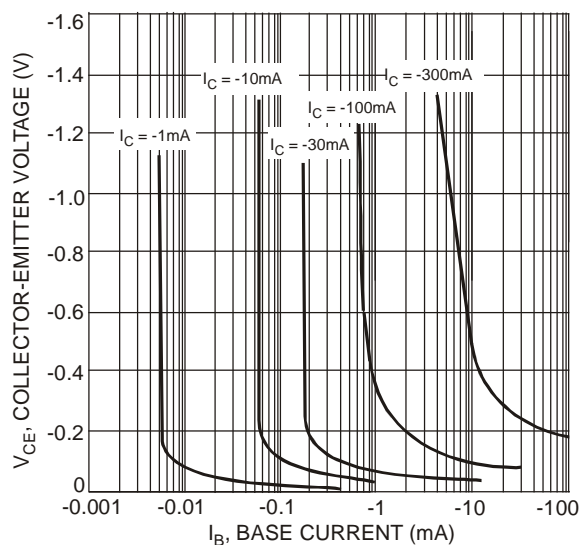


Fig. 5 Typical Collector Saturation Region

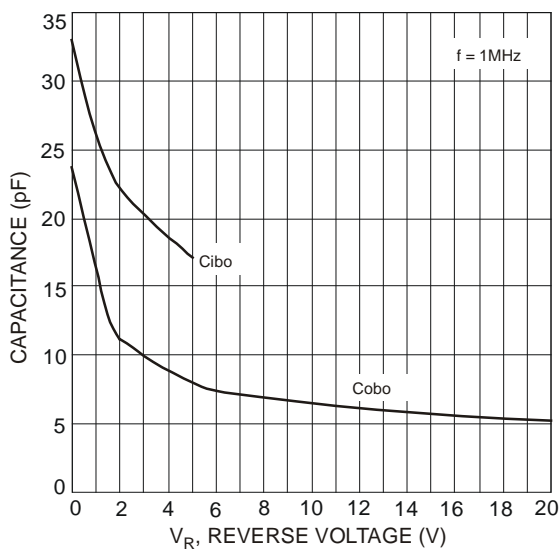
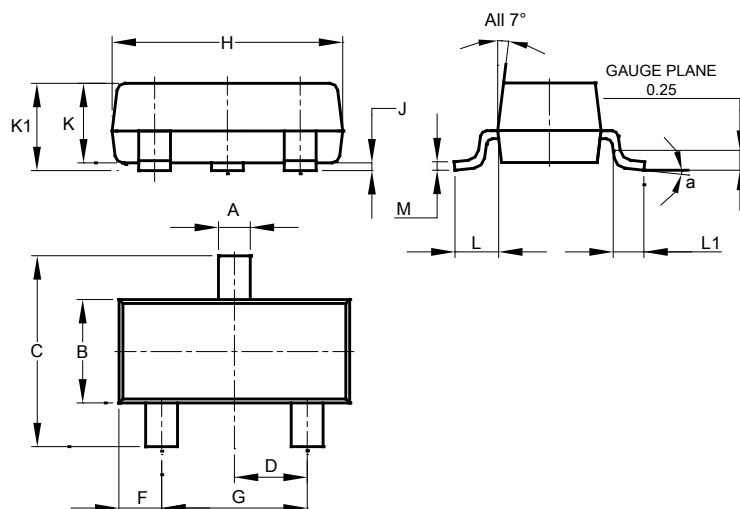


Fig. 6 Typical Capacitance Characteristics

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

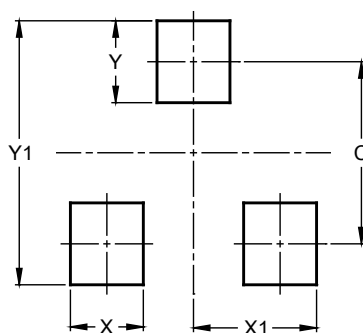


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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